Hone Group
Columbia University

Photolithography recipe of Slit for growth

Created by Changyao Chen **Date** Nov 4, 2007

General comment

Test

Mask

544um -> 120um

Photoresist: NR9-1000

Thickness: ~900nm

Spin speed /rpm: 4000

Acceleration: 10000

Tims /s: 60

Bake 150 degree for 1 min

☐ ***2nd Layer***

Photoresist:

Thickness:

Spin speed /rpm:

Acceleration:

Tims /s:

Bake degree for min

comment

Expose

Channel 1 | wavelength /nm 365

Time 1 Min | Power 6 mW

comment

☒ Postbake

Temperature /C 120 | Time 1 Min

comment

Develop

Developer RD-6

Time 10 Sec

comment

- ☐ **Rinse with IPA**
- ☒ **Rinse with DI water**
- ☐ **Rinse with other chemical**
- ☒ **Nitrogen flush**

comment

Test…

Save